

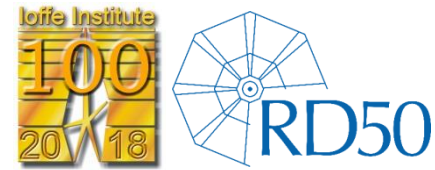


Novel view on extraction of charge carrier transport parameters from the data of classical TCT

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Motivation



TCT is the unique method
for investigation
of electric field distribution
in **heavily irradiated p-i-n** structures

TCT goal:

$$i(t) \rightarrow E(x), N_{eff}(x)$$

Ramo's theorem:

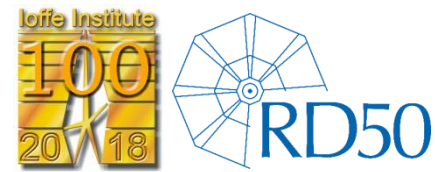
$$i(t) = E_w Q(t) v_{dr}(t)$$

There are some **problems**:

Pulse shape is determined by
a combination of a several factors:

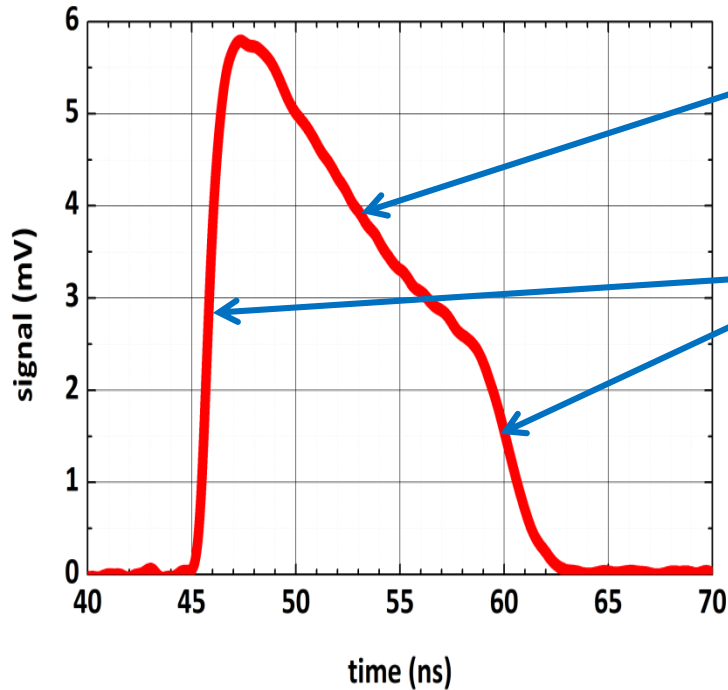
- $E(x), \mu(E(x)) \rightarrow v_{dr} = E(x(t)) \times \mu[E(x(t))]$
Drift velocity is a function of a several variables
- **The charge of drifting carriers is not constant in time**
 $Q = Q(t)$
Due to the carrier trapping on deep levels (τ_{tr})
- **Pulse edges distortions**
Due to the nonuniformity of generated cloud of carriers,
diffusion and response of the electric circuit

Outline



- ❖ Motivation
- ❖ Reconstruction of the physical response
- ❖ TCT Signal processing
- ❖ Numerical solution of the system of equations for the electric field
- ❖ Electric field reconstruction in nonirradiated detectors
- ❖ Electric field reconstruction in irradiated detectors
- ❖ Summary

TCT Pulse



$$i(t) = \frac{1}{d} \times Q(x(t)) \times v_{dr}(x(t), E(x(t)))$$

Distorted pulse edges

*in this case, key condition: $Q(x(t)) \equiv Q_0$

We want to obtain the electric field directly from the experimental data without a priori knowledge and any models

Typical TCT pulse of nonirradiated detector
Current induced by electron drift

Main equations for Electric field reconstruction

The lateral size of the detector's contacts is much bigger than thickness of sensitive area:
1D geometry

Current response

$$i(t) = \frac{Q(t)}{d} v_{dr}(t)$$

Mobility

$$\mu_{eff}(E) = \frac{\partial v_{dr}(E)}{\partial E}$$

Drift velocity

$$v_{dr}(t) = \mu(E(t))E(t)$$

Translation to coordinate scale

$$x(t) = \int_0^t v_{dr}(t') dt'$$

Collected charge

$$Q_0 = \int_0^{t_{dr}} i(t) dt$$

$\tau_{tr} \gg t_{dr}$ **only!**

Potential difference

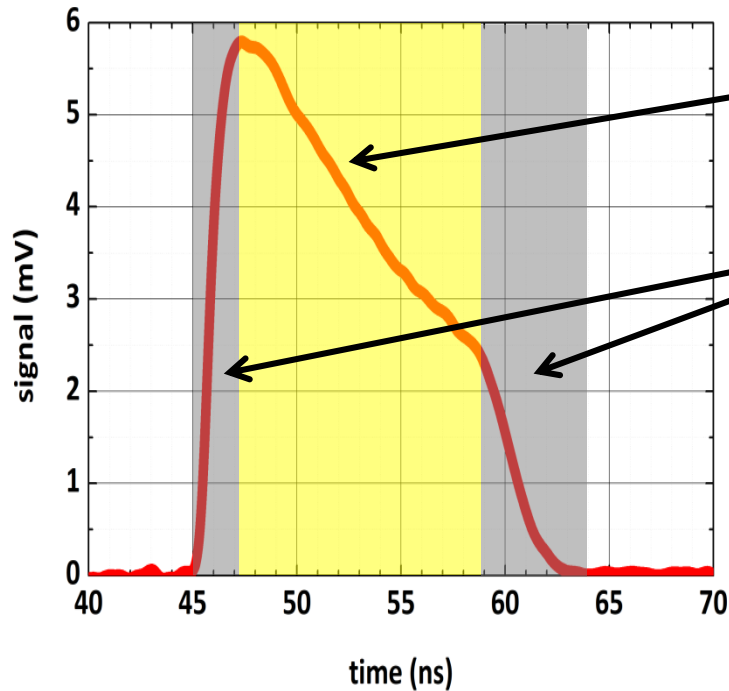
$$\Delta\varphi = \int_0^d E(x) dx = V_{bias}$$

Always!

All we need is solve this system...**but how?**

Simple criteria

Reconstruction of the $E(x)$ in the assumption of negligible carrier trapping



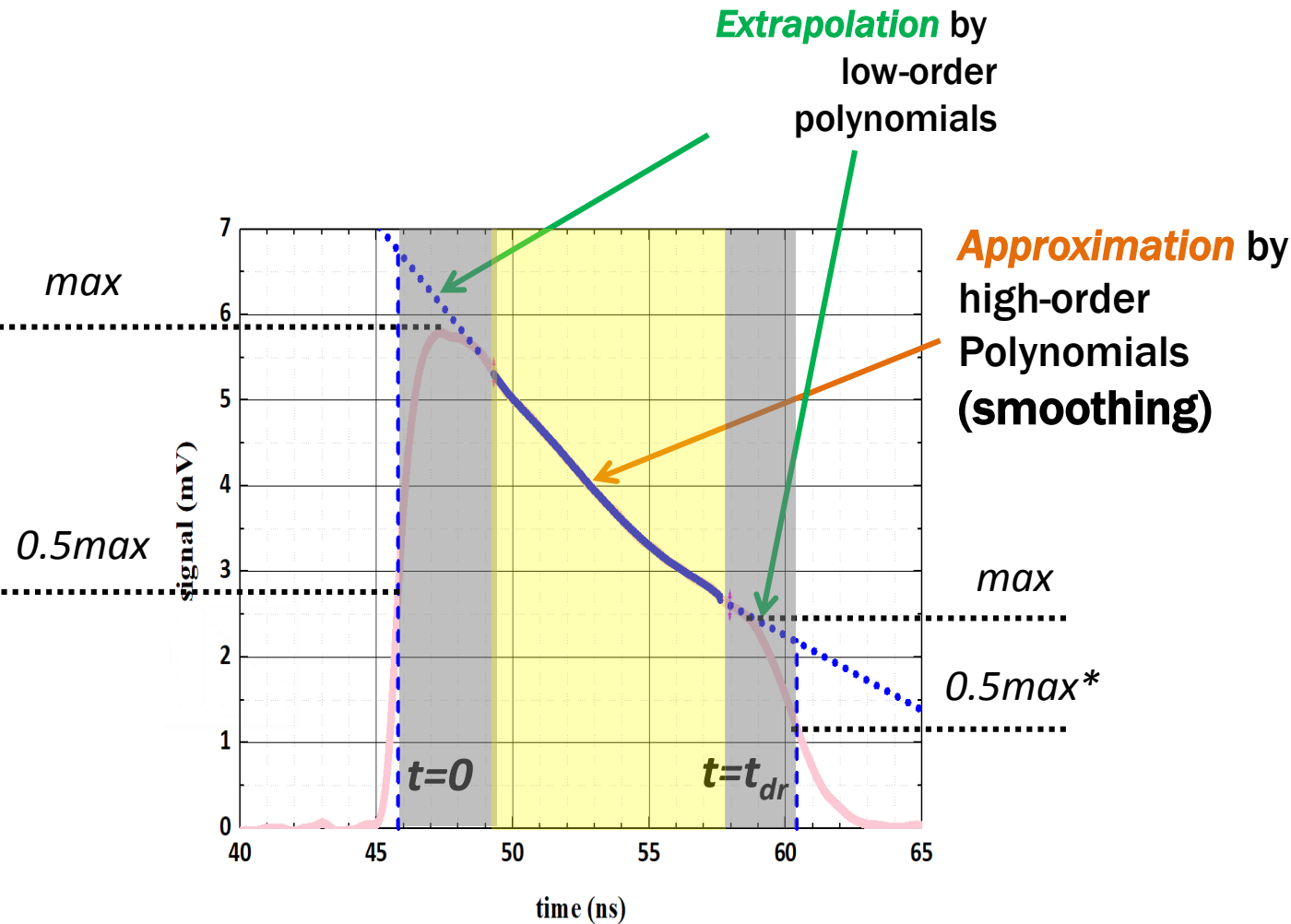
Gradual current reduction

Current response shape is strongly disturbed (gray regions)

$$\tau_{tr} \gg t_{dr}$$

Current pulse response of the full-depleted detector

Data processing: reconstruction of physical response



Criterion for the correctness:

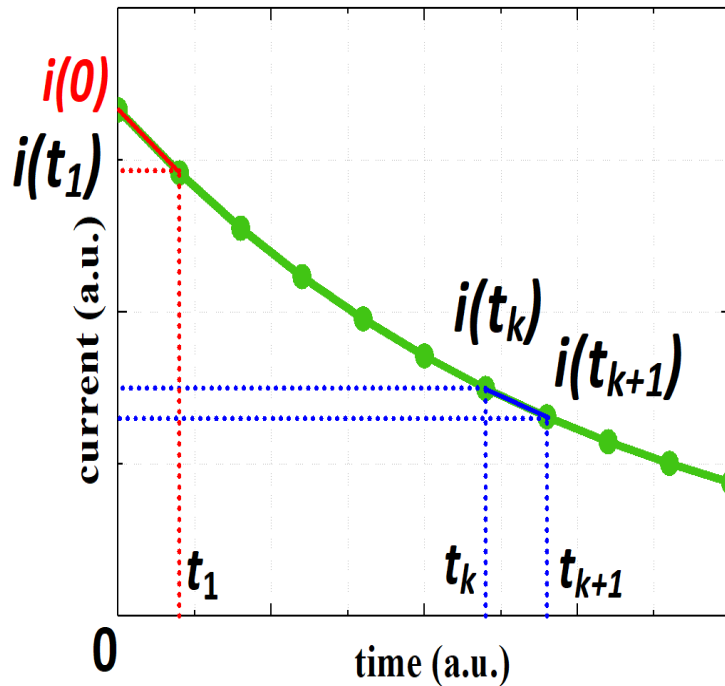
$$Q_0^{exp} = Q_0^{phys}$$



In the case of mistake

t_{dr} can be moved

We have the physical response, what's next?



Approach to the reconstruction of the $E(x)$ profile

$$E(0) = \frac{d}{Q_0 \times \mu} \times i(0) \quad \text{Initial condition}$$

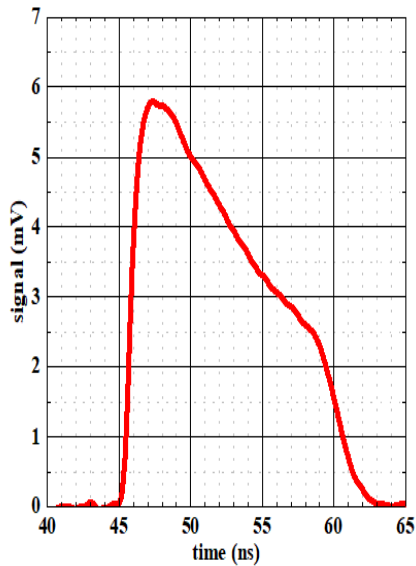
$$E_{k+1} = \frac{d}{Q_0} [i(t_{k+1}) - i(t_k)] \mu_{eff}(E_k) + E_k, \\ k = 0 \dots N - 1, \quad t_N = t_{dr}.$$

$$x_k(t_k) = \int_0^{t_k} v_{dr}(t) dt,$$

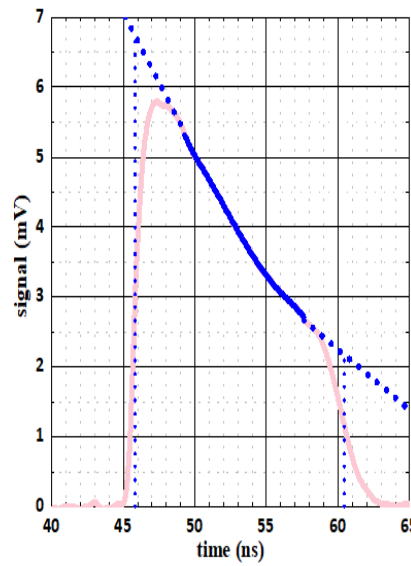
N.B. $\mu_{eff} = \text{const}$ in the interval $[i_k, i_{k+1})$

Reconstruction of $E(x)$

DATA



Physical response

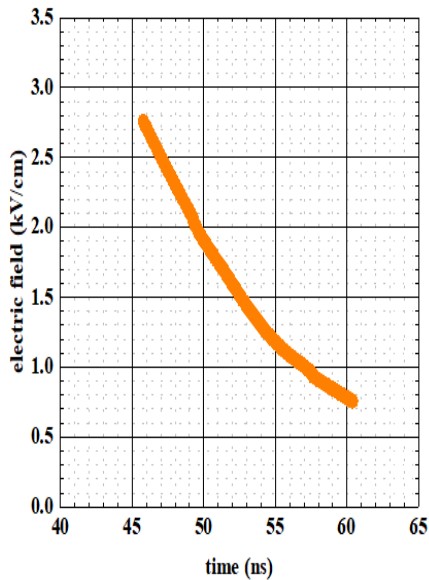


Correctness test:

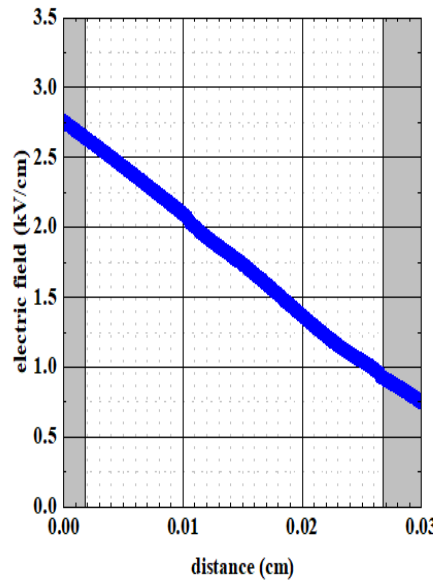
$$\Delta\varphi = \int_0^d E(x) dx = 52.2 V$$

only 4% larger than applied bias of 50 V

$E(t)$

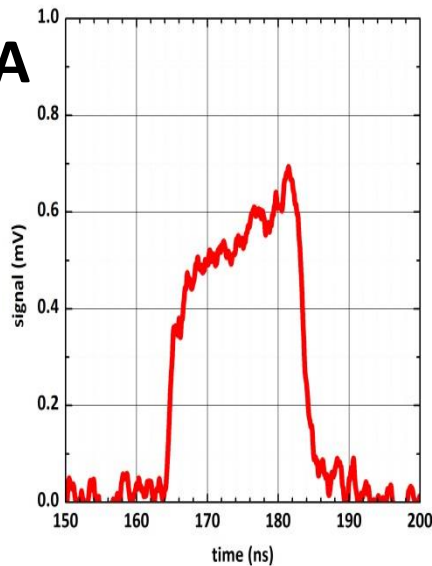


$E(x)$

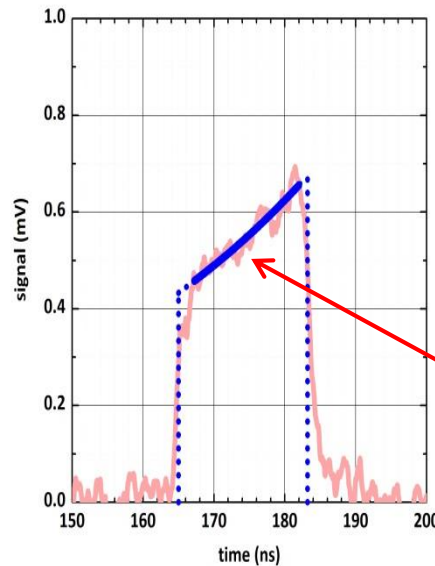


Hole current response

DATA

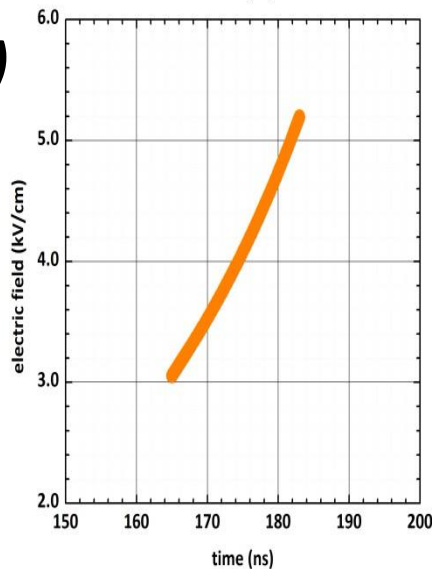


Physical response

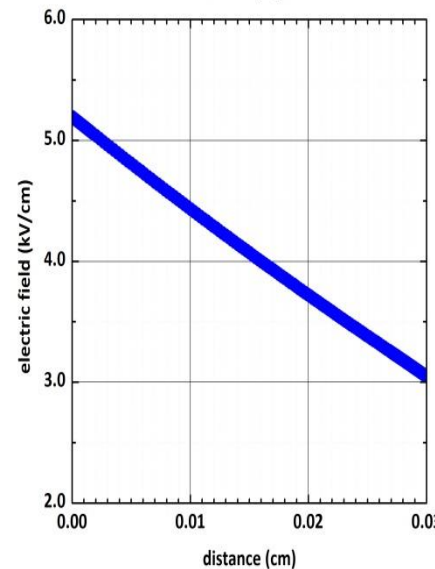


In this case, the correctness of smoothing is **really important** (suppression of fluctuations produced by noise)

$E(t)$



$E(x)$



Correctness test:

$$\Delta\varphi = \int_0^d E(x) dx = 101.3 \text{ V}$$

only 1% larger than applied bias of 100 V

Effective concentration

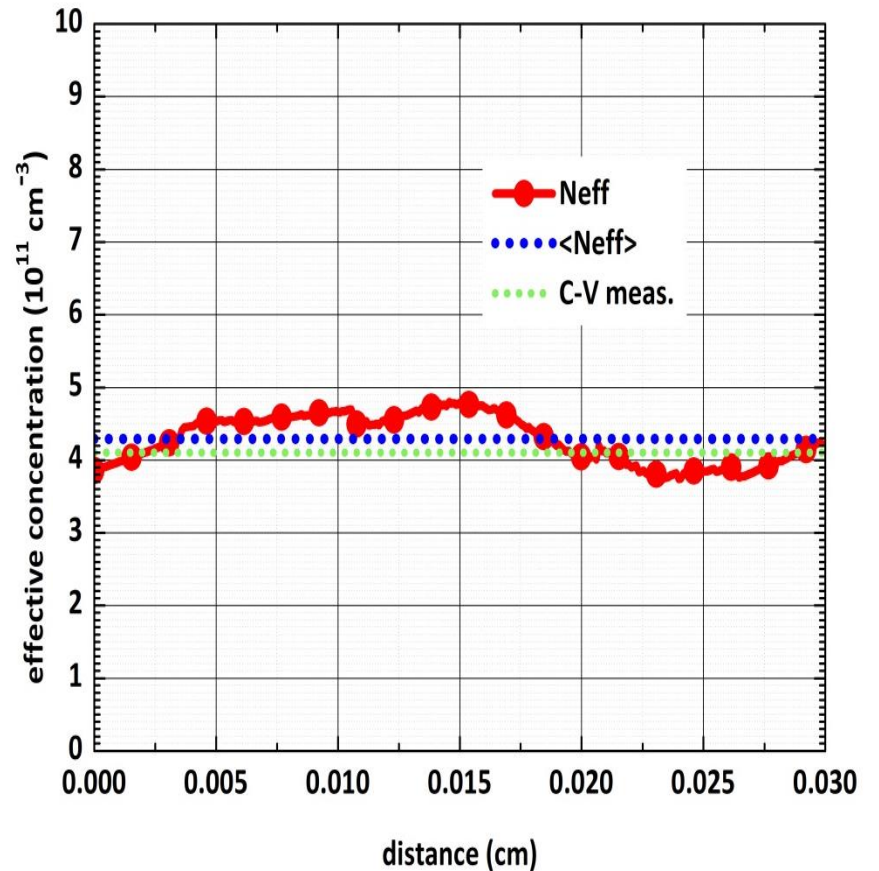
Poisson's eq.

$$E(x) \longrightarrow N_{eff}(x)$$

The profile of the effective concentration is close to **uniform**

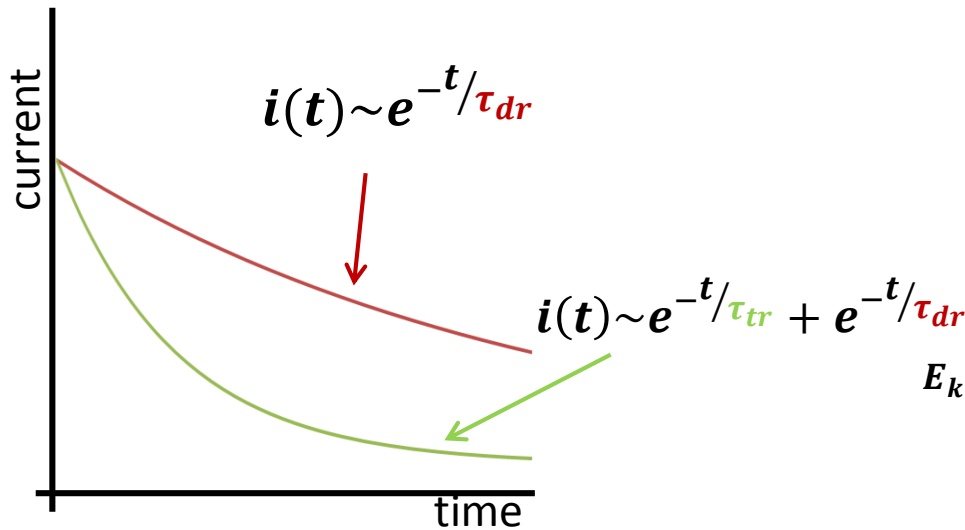
| Method | Electron current response | Hole current response | C-V |
|--|---------------------------|-----------------------|-----|
| N_{eff} (10^{11} cm^{-3}) | 4.3 | 4.0 | 4.1 |

Accuracy: $\sigma = 5\%$!



Carrier trapping

In irradiated *Si* detectors, the drifting charge decreases with time due to carrier **trapping** on the deep levels



$$\frac{1}{\tau_{tr}} = \beta \times F$$

↑ Trapping time constant
 ↑ Proportionality constant
 ↑ Fluence

However, the same procedure is applicable

TCT signal processing:

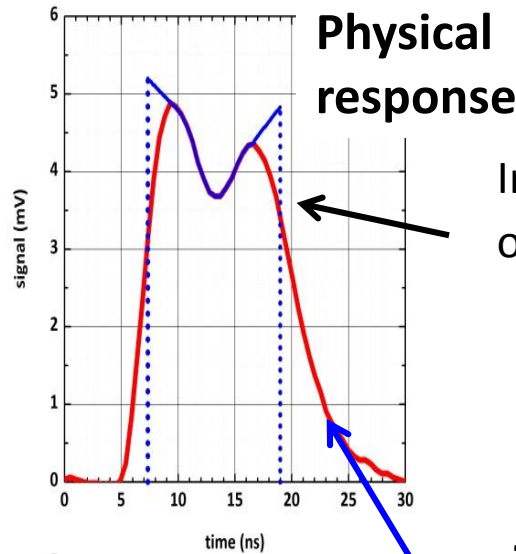
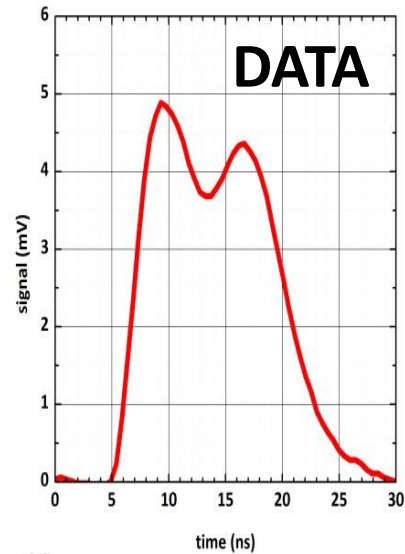
$$E_{k+1} = \frac{d}{Q_0 \exp\left(-\frac{t_{k+1}}{\tau_{tr}}\right)} [i(t_{k+1}) - i(t_k)] \mu_{eff}(E_k) + E_k,$$

$$k = 0 \dots N - 1, \quad t_N = t_{dr}.$$

N is the number of experimental points

Different processes have a **similar effect** on the pulse shape !

The same steps to the E(x) reconstruction



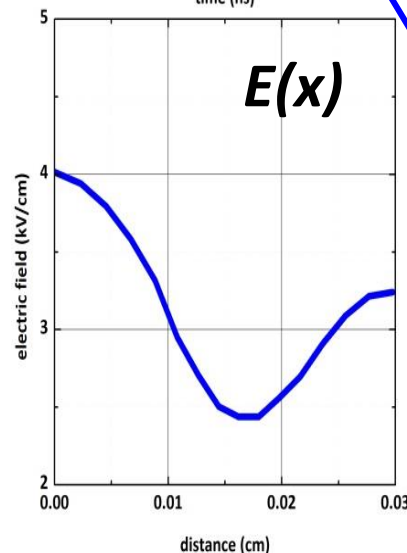
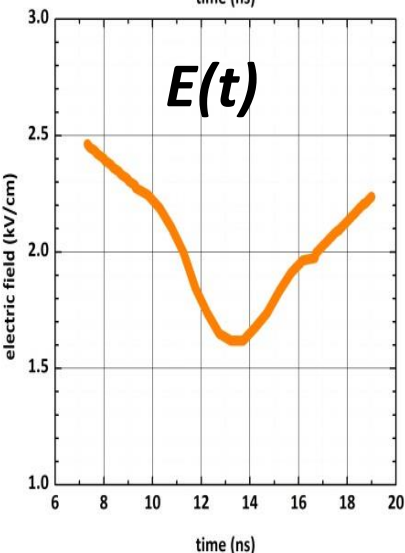
In this case, **we can't** use a criterion of Q_0 and only $\Delta\varphi$ isn't affected by charge trapping!

$$d = \int_0^{t_{dr}} v_{dr}(t) dt$$

$$\int_0^{t_{dr}} v_{dr}(t) dt E(x) dx = 80 V \rightarrow t_{dr} = 12 ns!$$

t_{dr} is not on the level of half-amplitude!

The long tail in the response is not connected with the carrier drift and can be explained by the fast trapping/detrapping. The criterion of potential difference shows it!



Irradiated Si detector

p⁺/n/n⁺ pad detector

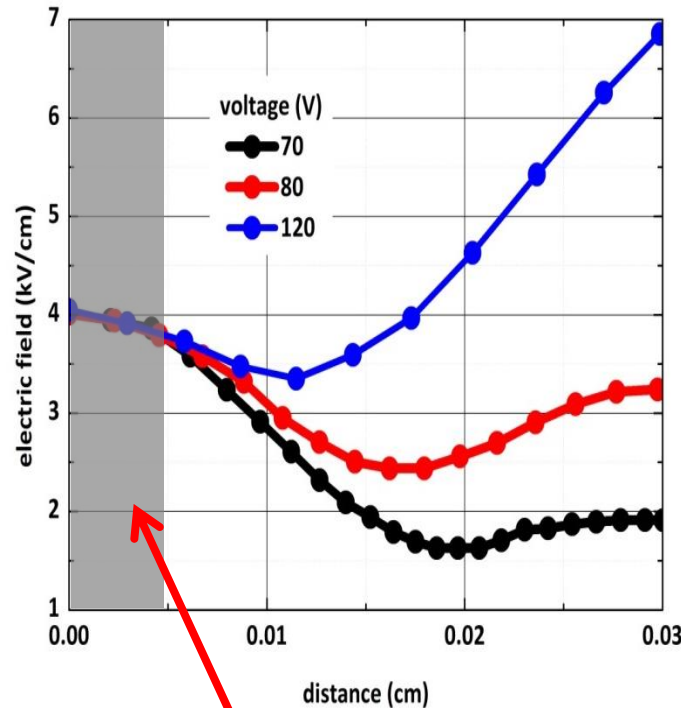
$d = 300 \mu\text{m}$

$N_D = 5 \times 10^{11} \text{cm}^{-3}$

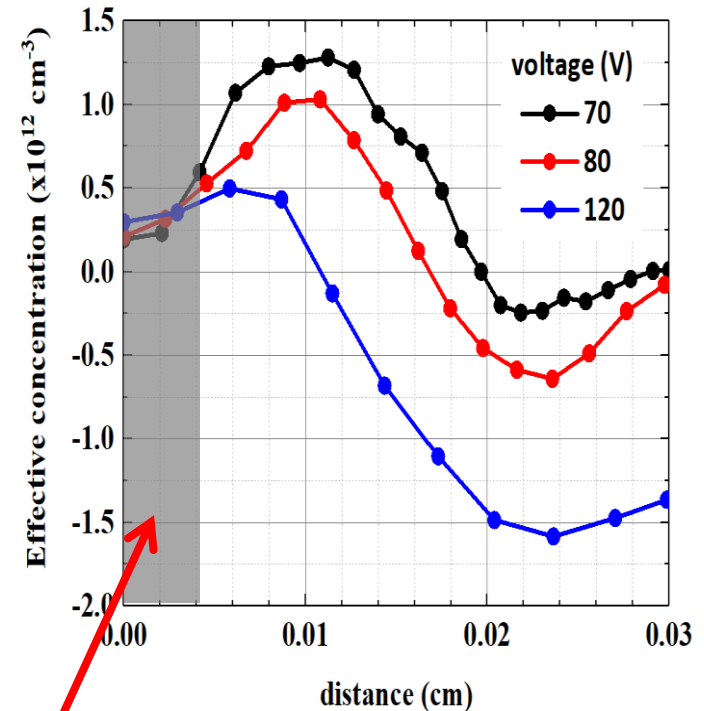
Irradiated by protons

$F = 4 \times 10^{14} \text{cm}^{-2}$

Electric field

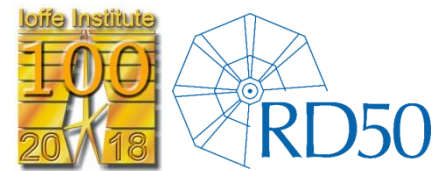


Effective concentration



Area of uncertainty (area of extrapolation)

Summary



- The new approach is proposed for obtaining the $E(x)$ and $N_{eff}(x)$ from TCT data. It based on the reconstruction of physical response and numerical solution of the system of transport equations.
- In the case of nonirradiated detector, $E(x)$ and $N_{eff}(x)$ were obtained. They are close to uniform and their mean values equal with 5% accuracy to the results of the C-V measurements.
- The described algorithm was applied to responses of irradiated detectors. In this case, temporal resolution and pulse approximation is critical.

Thank you for attention!